N-Channel Silicon MOSFET



2SK1444LS

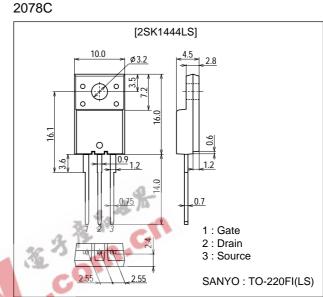
# **Ultrahigh-Speed Switching Applications**

## Features

- · Low ON-resistance.
- Ultrahigh-speed switching.
- · Micaless package facilitating mounting.

## **Package Dimensions**

unit : mm



## **Specifications**

#### Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol		Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS			450	V
Gate-to-Source Voltage	VGSS			±30	V
Drain Current (DC)	ID			3	А
Drain Current (Pulse)	IDP	PW≤10µ	s, duty cycle≤1%	12	А
Allowable Power Dissipation	PD			2.0	W
		Tc=25°C		25	W
Channel Temperature	Tch			150	°C
Storage Temperature	Tstg			-55 to +150	°C

### Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
		Conditions	min	typ	max	Unit
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0	450			V
Zero-Gate Voltage Drain Current	IDSS	VDS=450V, VGS=0			1.0	mA
Gate-to-Source Leakage Current	IGSS	V <sub>GS</sub> =±30V, V <sub>DS</sub> =0			±100	nA

(Note) Be careful in handling the 2SK1444LS because it has no protection diode between gate and source.

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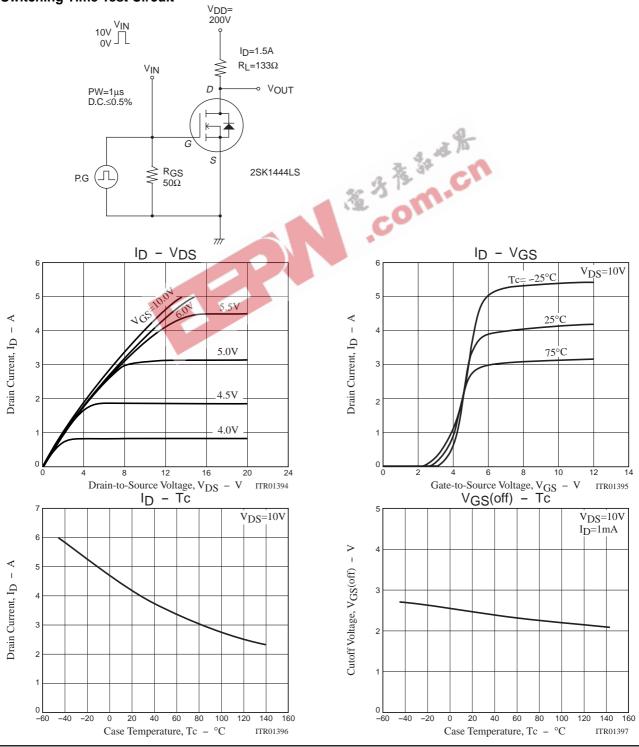
Marking: K1444

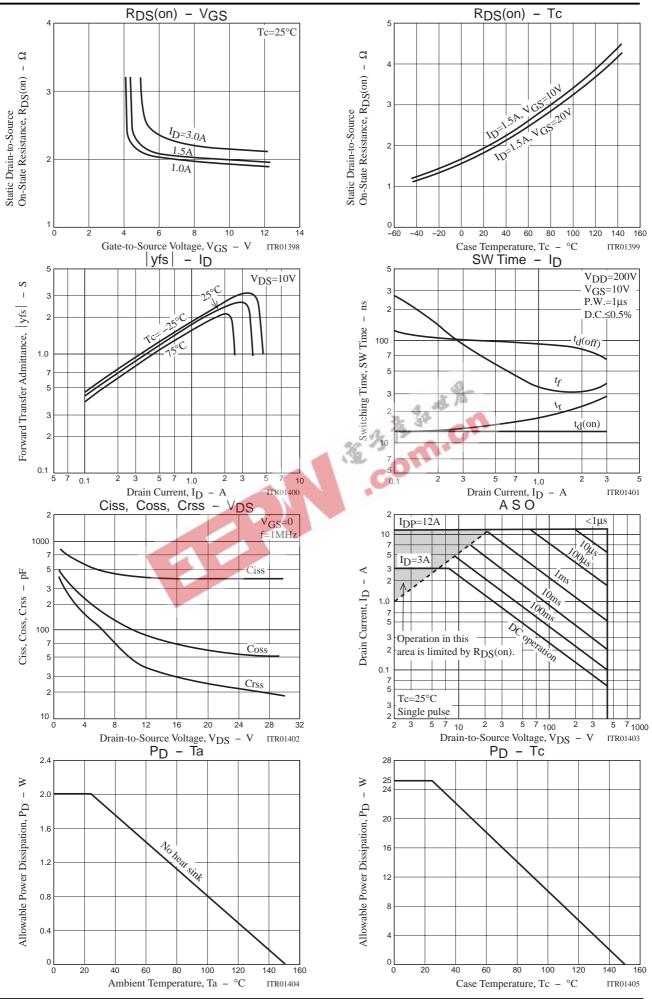
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Parameter	Symbol	Conditions	Ratings			Unit
Falameter		Conditions	min	typ	max	Unit
Cutoff Voltage	VGS(off)	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	2.0		3.0	V
Forward Transfer Admittance	yfs	V <sub>DS</sub> =10V, I <sub>D</sub> =0.5A	1.1	2.2		S
Static Drain-to-Source On-State Resistance	RDS(on)	ID=0.5A, VGS=10V		2.0	2.6	Ω
Input Capacitance	Ciss	V <sub>DS</sub> =20V, f=1MHz		400		pF
Output Capacitance	Coss	V <sub>DS</sub> =20V, f=1MHz		60		pF
Reverse Transfer Capacitance	Crss	VDS=20V, f=1MHz		25		pF
Turn-ON Delay Time	t <sub>d</sub> (on)	See specified Test Circuit.		12		ns
Rise Time	tr	See specified Test Circuit.		20		ns
Turn-OFF Delay Time	t <sub>d</sub> (off)	See specified Test Circuit.		80		ns
Fall Time	tf	See specified Test Circuit.		35		ns
Diode Forward Voltage	V <sub>SD</sub>	IS=3A, VGS=0			1.8	V

## Switching Time Test Circuit





No.3447-3/4

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